## ECE 255 Spring 2019

Homework 4

## Due 5:00 PM Monday, Feb. 4 in Dropbox

1) Consider the circuit shown below with $\mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega, \mathrm{V}_{\mathrm{CC}}=3 \mathrm{~V}$, and $\mathrm{v}_{\mathrm{s}} \ll \mathrm{V}_{\mathrm{CC}}$. In forward bias, the diode can be approximated by $\mathrm{V}_{\mathrm{D}}=0.7 \mathrm{~V}$. Assume $T=300 \mathrm{~K}$ so that $V_{T}=0.026$ V.
a) First, consider the DC operating point. Find the value of the diode current, $\mathrm{I}_{\mathrm{D}}$.
b) Next, consider the ac small-signal model. What is the value of $r_{d}$ at this operating point?
c) What is the magnitude of the smallsignal diode current, $i_{d}$, in terms of $\mathrm{v}_{\mathrm{s}}$ ?
d) What is the magnitude of the smallsignal voltage across the diode, $\mathrm{v}_{\mathrm{d}}$, in terms of $v_{s}$ ?

2) Consider an NPN transistor with the voltages below applied. Identify the region of operation for each case (Active, saturation, or cut-off).

| Case | Emitter | Base | Collector | Region |
| :--- | :--- | :--- | :--- | :--- |
| 1 | 0 | +0.7 | +1.0 |  |
| 2 | 0 | +0.7 | +0.1 |  |
| 3 | -0.8 | 0 | +3.0 |  |
| 4 | -0.7 | 0 | -0.5 |  |
| 5 | +1.5 | +2.2 | +3.0 |  |
| 6 | +1.0 | 0 | +3.0 |  |

HW 4 (continued)
3) Consider a PNP transistor with the voltages below applied. Identify the region of operation for each case (Active, saturation, or cut-off).

| Case | Emitter | Base | Collector | Region |
| :--- | :--- | :--- | :--- | :--- |
| 1 | 0 | -0.7 | -1.0 |  |
| 2 | 0 | -0.7 | -0.2 |  |
| 3 | +0.7 | 0 | -3.0 |  |
| 4 | +0.7 | 0 | +0.5 |  |
| 5 | +1.5 | +0.8 | -2.0 |  |
| 6 | -1.0 | 0 | -3.0 |  |

4) Consider an NPN transistor in the active region with $V_{B E}=0.78 \mathrm{~V}$ at $I_{C}=6 \mathrm{~mA}$. Answer the following questions. Assume $T=300 \mathrm{~K}$ so that $V_{T}=0.026 \mathrm{~V}$.
a) What is the current at $V_{B E}=0.72 \mathrm{~V}$ ?
b) What is $V_{B E}$ at $I_{C}=6 \mu \mathrm{~A}$ ?
5) For an NPN transistor in the active region, we measure $I_{C}=0.7 \mathrm{~mA}$ and $I_{B}=20 \mu \mathrm{~A}$. Answer the following questions.

5a) What is $\beta$ ?
5b) What is $\alpha$ ?
5c) What is $I_{E}$ ?
6) For the circuit below, you may also assume that $V_{B E}=0.7 \mathrm{~V}$ and that all transistors operate in the active mode. The voltages, $\mathrm{V}_{1}-\mathrm{V}_{5}$, on this figure are voltage probes - places that we want to determine the voltage - they are NOT voltage sources. Answer the following questions:

5a) Assume that $\beta \rightarrow \infty$ (i.e. ignore base currents) and compute the five voltages labeled in the figure. Also, verify that the two transistors are biased in the active mode.

5b) Assume that $\beta=50$, and compute the five voltages labeled in the figure.

HW4 (continued)

7) Consider the npn BJT circuit shown below, with an ideal current source providing $\mathrm{I}_{\mathrm{B}}$.

For parts a)-c), use $\mathrm{R}_{\mathrm{C}}=12 \mathrm{k} \Omega$ and assume that the BJT operates in forward active mode.
a) What is the value of $\mathrm{I}_{\mathrm{C}}$ ?
b) What is the value of $\mathrm{V}_{\mathrm{CE}}$ ?
c) What is the value of $V_{B C}$ ?
d) In this part only, assume that $R_{C}$ can be varied. What is the maximum value for $\mathrm{R}_{\mathrm{C}}$ such that the transistor remains in forward active mode, i.e. that the B-C junction remains reverse biased?


